

SPECIFICATION OF LED CHIP
C660-55
[RED]

1) Commodity Type and Physical Characteristics.

- | | | | |
|----------------------|--------------------|-------------------|------------------|
| 1. Material | GaAlAs/GaAlAs(DDH) | | |
| 2. Electrode | Top Side | N (cathode)side | :Au Alloy/Al Pad |
| | Bottom Side | P (anode)side | :Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.8	2.1	V
		If=100mA		2.1	2.3	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA		40		mcd
Power Intensity	Po	If=20mA	1.5	2.5		mW
		If=100mA	7.5	12.5		
Peak Wavelength	λ_P	If=20mA	645	655	665	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		20		nm
Rise Time	tr	If=20mA		100		ns
Fall Time	tf	If=20mA		100		ns

‡ Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

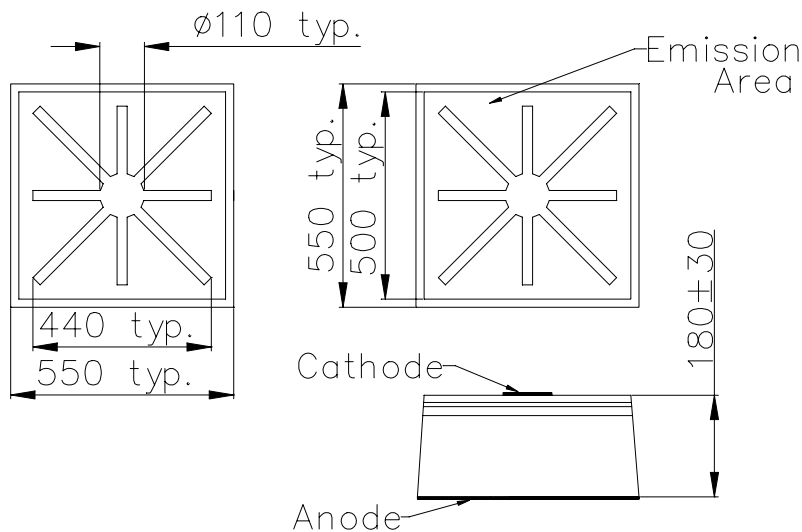


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area